

Amended claims:

- B1*
1. (Amended) A device formed in a semiconductor material of a first conductivity type, the semiconductor material having a dopant concentration, the device comprising:
 a well of a second conductivity type formed in the semiconductor material, the well having a dopant concentration;
 a first region of the second conductivity type formed in the well, the first region having a dopant concentration greater than the dopant concentration of the well, the first region being connected to a first node;
 a second region of the first conductivity type formed in the well, the second region having a dopant concentration greater than the dopant concentration of the semiconductor material, the second region being connected to the first node;
 a third region of the second conductivity type formed in the semiconductor material, the third region having a dopant concentration greater than the dopant concentration of the well, the third region being connected to a second node, and
 a fourth region of the first conductivity type formed in the semiconductor material, the fourth region having a dopant concentration greater than the dopant concentration of the semiconductor material, the fourth region being connected to the second node,
 wherein the second region is reduced in size compared to a conventional LVTSCR of the same process.
- B2*
3. (Amended) The device of claim 2, wherein the third region is increased in size relative to that of a conventional LVTSCR of the same process, to reduce space charge neutralization.
- B3*
9. (Amended) A method of providing a device having a higher holding voltage than a LVTSCR and supporting a higher current than a GGNMOS, comprising providing a LVTSCR-like structure having a p+ emitter that is sufficiently reduced in size so as to increase the holding voltage to a desired level.
- B4*
11. A method of creating an ESD protection structure having a higher holding voltage than a conventional LVTSCR, comprising
 providing a LVTSCR-like structure, and
 manipulating the size of the p+ emitter.
12. A method of claim 11, further comprising using TCAD simulations to determine a p+ emitter size corresponding to a desired holding voltage.
13. A method of creating an ESD protection structure that supports a higher current than a conventional GGNMOS device, comprising
 providing a LVTSCR-like structure, and
 manipulating the size of the p+ emitter.
14. A method of claim 13, further comprising using TCAD simulations to determine a p+ emitter size corresponding to a desired current.
15. A method of varying the holding voltage of a LVTSCR, comprising
 adjusting the size of the p+ emitter.

16. A method of claim 15, further comprising adjusting the size of the n+ emitter.
17. A method of adjusting the holding voltage of an ESD protection structure that includes a semiconductor material of a first conductivity type, the semiconductor material having a dopant concentration; a well of a second conductivity type formed in the semiconductor material, the well having a dopant concentration; a first region of the second conductivity type formed in the well, the first region having a dopant concentration greater than the dopant concentration of the well, the first region being connected to a first node; a second region of the first conductivity type formed in the well, the second region having a dopant concentration greater than the dopant concentration of the semiconductor material, the second region being connected to the first node; a third region of the second conductivity type formed in the semiconductor material, the third region having a dopant concentration greater than the dopant concentration of the well, the third region being connected to a second node, and a fourth region of the first conductivity type formed in the semiconductor material, the fourth region having a dopant concentration greater than the dopant concentration of the semiconductor material, the fourth region being connected to the second node, comprising, adjusting the size of the second region.
18. A method of claim 17, further comprising adjusting the size of the third region.

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